

# Cascadable Silicon Bipolar MMIC Amplifier

## Technical Data

### MSA-0170

#### Features

- **Cascadable 50 Ω Gain Block**
- **3 dB Bandwidth:**  
DC to 1.3 GHz
- **High Gain:**  
18.5 dB Typical at 0.5 GHz
- **Unconditionally Stable**  
( $k > 1$ )
- **Hermetic Gold-ceramic  
Microstrip Package**

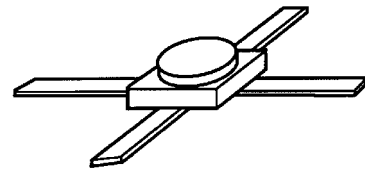
#### Description

The MSA-0170 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a hermetic high reliability package. This MMIC is

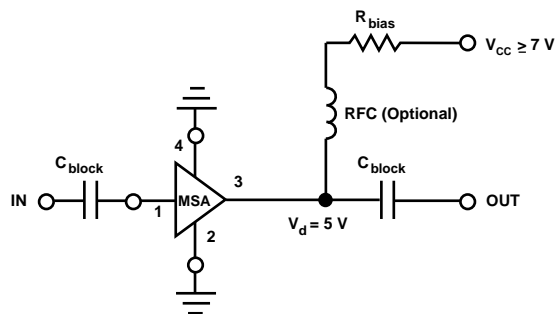
designed for use as a general purpose 50 Ω gain block. Typical applications include narrow and broad band IF and RF amplifiers in industrial and military applications.

The MSA-series is fabricated using HP's 10 GHz  $f_T$ , 25 GHz  $f_{MAX}$  silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

#### 70 mil Package



#### Typical Biasing Configuration



### MSA-0170 Absolute Maximum Ratings

Parameter	Absolute Maximum <sup>[1]</sup>
Device Current	40 mA
Power Dissipation <sup>[2,3]</sup>	200 mW
RF Input Power	+13 dBm
Junction Temperature	200°C
Storage Temperature	-65 to 200°C

#### Thermal Resistance<sup>[2,4]</sup>:

$$\theta_{jc} = 125^{\circ}\text{C}/\text{W}$$

#### Notes:

1. Permanent damage may occur if any of these limits are exceeded.
2.  $T_{\text{CASE}} = 25^{\circ}\text{C}$ .
3. Derate at  $8 \text{ mW}/^{\circ}\text{C}$  for  $T_{\text{C}} > 175^{\circ}\text{C}$ .
4. The small spot size of this technique results in a higher, though more accurate determination of  $\theta_{jc}$  than do alternate methods. See MEASUREMENTS section "Thermal Resistance" for more information.

### MSA-0170 Electrical Specifications<sup>[1]</sup>, $T_{\text{A}} = 25^{\circ}\text{C}$

Symbol	Parameters and Test Conditions: $I_{\text{d}} = 17 \text{ mA}$ , $Z_{\text{o}} = 50 \Omega$	Units	Min.	Typ.	Max.
$G_{\text{P}}$	Power Gain ( $ S_{21} ^2$ ) $f = 0.1 \text{ GHz}$	dB	18.0	19.0	
$\Delta G_{\text{P}}$	Gain Flatness $f = 0.1 \text{ to } 0.7 \text{ GHz}$	dB		$\pm 0.6$	
$f_{3 \text{ dB}}$	3 dB Bandwidth	GHz		1.3	
VSWR	Input VSWR $f = 0.1 \text{ to } 3.0 \text{ GHz}$			1.3:1	
	Output VSWR $f = 0.1 \text{ to } 3.0 \text{ GHz}$			1.3:1	
NF	50 $\Omega$ Noise Figure $f = 0.5 \text{ GHz}$	dB		5.5	
$P_{1 \text{ dB}}$	Output Power at 1 dB Gain Compression $f = 0.5 \text{ GHz}$	dBm		1.5	
$\text{IP}_3$	Third Order Intercept Point $f = 0.5 \text{ GHz}$	dBm		14.0	
$t_{\text{D}}$	Group Delay $f = 0.5 \text{ GHz}$	psec		150	
$V_{\text{d}}$	Device Voltage	V	4.5	5.0	5.5
$dV/dT$	Device Voltage Temperature Coefficient	mV/ $^{\circ}\text{C}$		-9.0	

#### Note:

1. The recommended operating current range for this device is 13 to 25 mA. Typical performance as a function of current is on the following page.

### MSA-0170 Typical Scattering Parameters ( $Z_0 = 50 \Omega$ , $T_A = 25^\circ\text{C}$ , $I_d = 17 \text{ mA}$ )

Freq. GHz	S <sub>11</sub>		S <sub>21</sub>			S <sub>12</sub>			S <sub>22</sub>	
	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang
0.1	.08	171	19.0	8.88	173	-22.7	.073	2	.10	-13
0.2	.07	161	18.9	8.77	167	-22.5	.075	6	.11	-27
0.3	.07	152	18.7	8.64	160	-22.3	.077	8	.10	-39
0.4	.06	143	18.5	8.45	153	-22.4	.076	11	.11	-49
0.5	.05	133	18.3	8.23	147	-22.0	.079	13	.11	-59
0.6	.04	115	18.0	7.98	141	-21.8	.081	17	.12	-67
0.8	.03	79	17.5	7.46	130	-21.2	.087	20	.12	-83
1.0	.04	-14	16.8	6.90	119	-20.2	.098	23	.12	-96
1.5	.08	-52	15.0	5.64	96	-19.0	.112	26	.10	-116
2.0	.12	-87	13.2	4.58	78	-17.7	.131	24	.08	-134
2.5	.15	-112	11.7	3.85	67	-16.7	.147	25	.07	-135
3.0	.19	-132	10.3	3.27	54	-16.1	.156	22	.07	-129
3.5	.24	-148	8.9	2.80	41	-15.4	.170	18	.09	-117
4.0	.26	-159	7.7	2.43	29	-15.0	.177	13	.13	-106
4.5	.27	-170	6.6	2.14	18	-14.7	.184	8	.17	-105
5.0	.27	175	5.7	1.92	8	-14.3	.192	5	.20	-106

A model for this device is available in the DEVICE MODELS section.

### MSA-0170 Typical Performance, $T_A = 25^\circ\text{C}$

(unless otherwise noted)

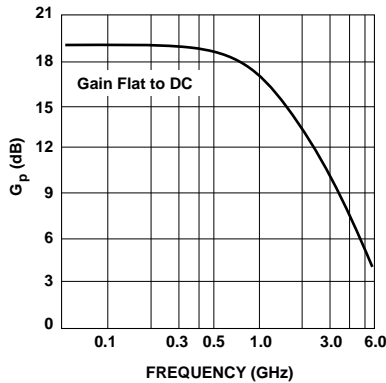


Figure 1. Typical Power Gain vs. Frequency,  $T_A = 25^\circ\text{C}$ ,  $I_d = 17 \text{ mA}$ .

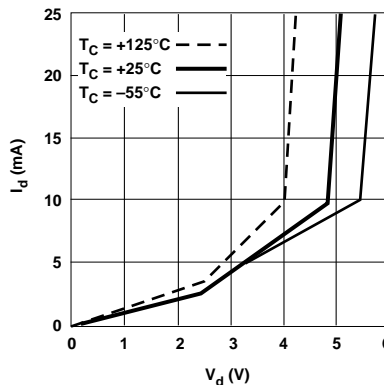


Figure 2. Device Current vs. Voltage.

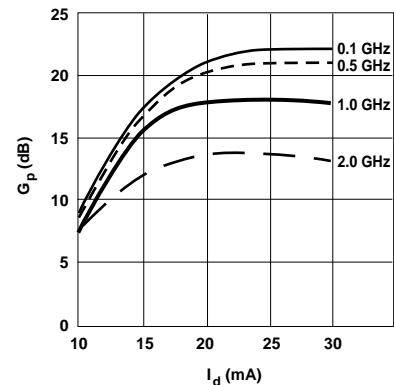


Figure 3. Power Gain vs. Current.

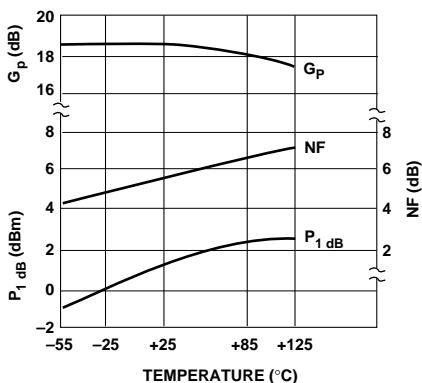


Figure 4. Output Power at 1 dB Gain Compression, NF and Power Gain vs. Case Temperature,  $f = 0.5 \text{ GHz}$ ,  $I_d = 17 \text{ mA}$ .

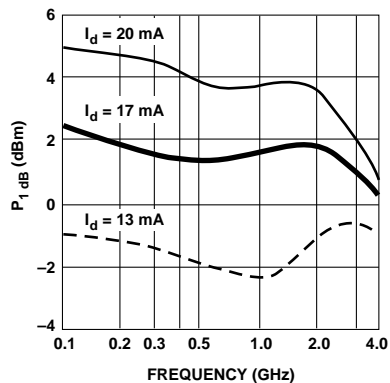


Figure 5. Output Power at 1 dB Gain Compression vs. Frequency.

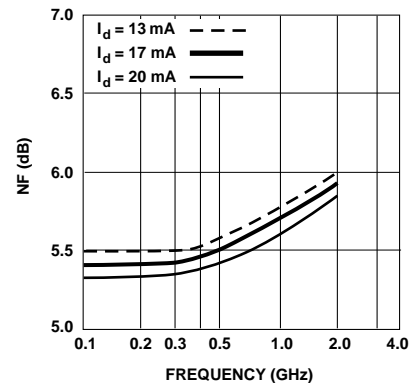
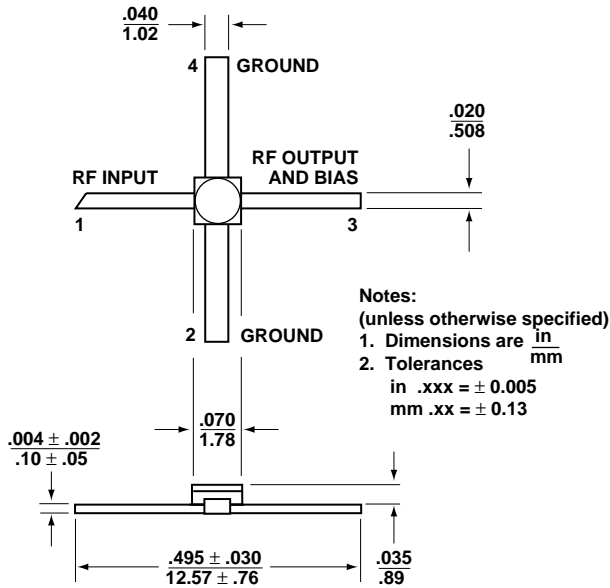


Figure 6. Noise Figure vs. Frequency.

## 70 mil Package Dimensions



[www.hp.com/go/rf](http://www.hp.com/go/rf)

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